ON Semiconductor

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MOSFET - Power, Single N-Channel

100 V, 12.9 mΩ, 42 A

STTFS015N10MCL

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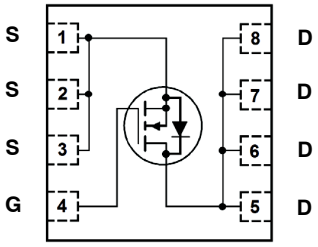
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$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
100 V	12.9 mΩ @ 10 V	42 A
	19.8 mΩ @ 4.5 V	

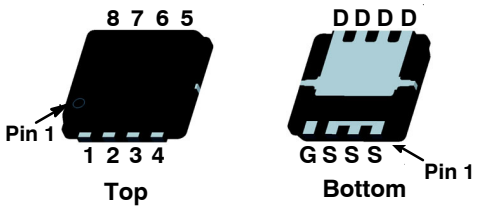
Features

- Small Footprint (3.3x3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Primary DC−DC MOSFET
- Synchronous Rectifier in DC−DC and AC−DC
- Motor Drive
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ELECTRICAL CONNECTION



N-Channel MOSFET



WDFN8
(3.3x3.3, 0.65 P)
CASE 511DY

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	100	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	T_C = 25°C	I_D	42	A
		T_C = 100°C		27	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	45	W
		T_C = 100°C		18	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	T_A = 25°C	I_D	10	A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	P_D	2.5	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	130	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +150	°C
Single Pulse Drain−to−Source Avalanche Energy (L = 3 mH, I_{AS} = 6 A)			E_{AS}	54	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

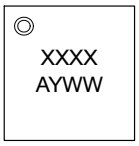
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State	$R_{\theta JC}$	2.8	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	50	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

MARKING DIAGRAM



XXXX	= Device Code
A	= Assembly Location
Y	= Year Code
WW	= Work Week Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

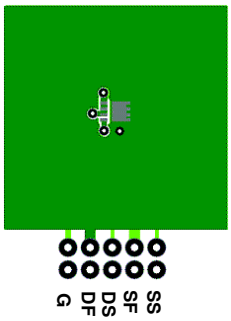
Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				60		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 100 V	T_J = 25 °C			1.0	μA
			T_J = 125°C			250	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 77 μA		1	1.45	3	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−5.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 14 A		10.6	12.9	mΩ
		V_{GS} = 4.5 V	I_D = 11 A		14.4	19.8	
Forward Transconductance	g_{FS}	V_{DS} =5 V, I_D = 14 A			50		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 50 V			1338		pF
Output Capacitance	C_{OSS}				521		
Reverse Transfer Capacitance	C_{RSS}				9.0		
Gate Resistance	R_G			0.1	0.5	1	Ω
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 50 V; I_D = 14 A			9.0		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 50 V; I_D = 14 A			19		nC
Threshold Gate Charge	$Q_{G(TH)}$	V_{GS} = 10 V, V_{DS} = 50 V; I_D = 14 A			2.0		nC
Gate−to−Source Charge	Q_{GS}				3.0		
Gate−to−Drain Charge	Q_{GD}				3.0		
Plateau Voltage	V_{GP}				2.7		V
Output Charge	Q_{OSS}	V_{GS} = 0 V, V_{DS} = 50 V			35		nC
Total Gate Charge Sync	Q_{SYNC}	V_{GS} = 0 to 10 V, V_{DS} = 0 V			17		nC
SWITCHING CHARACTERISTICS (Note 5)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 14 A, R_G = 6.0 Ω			9.0		ns
Rise Time	t_r				10		
Turn−Off Delay Time	$t_{d(OFF)}$				25		
Fall Time	t_f				5.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Source to Drain Diode Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = 2 A	(Note 7)		0.7	1.2	V
		V_{GS} = 0 V, I_S = 14 A	(Note 7)		0.83	1.3	
Reverse Recovery Time	t_{rr}	I_F = 7 A, di/dt = 300 A/μs			20		ns
Reverse Recovery Charge	Q_{rr}				33		nC
Reverse Recovery Time	t_{rr}	I_F = 7 A, di/dt = 1000 A/μs			14		ns
Reverse Recovery Charge	Q_{rr}				76		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

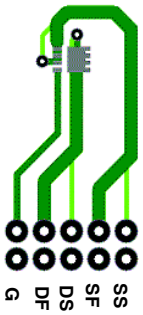
4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

NOTES:

6. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad of 2 oz copper.

7. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
8. E_{AS} of 54 mJ is based on starting T_J = 25°C; L = 3 mH, I_{AS} = 6 A, V_{DD} = 100 V, V_{GS} = 10 V.
9. Pulsed I_D please refer to Figure 11 SOA graph for more details.
10. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro−mechanical application board design.

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping†
STTFS015N10MCL	S15L	WDFN8 (3.3x3.3) (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

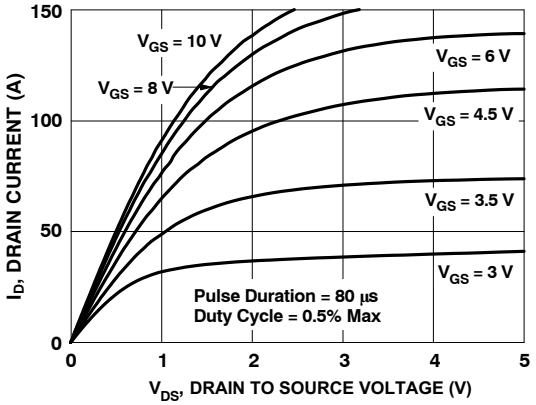


Figure 1. On Region Characteristics

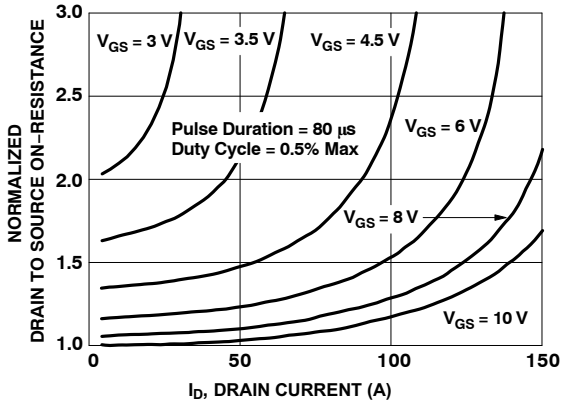


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

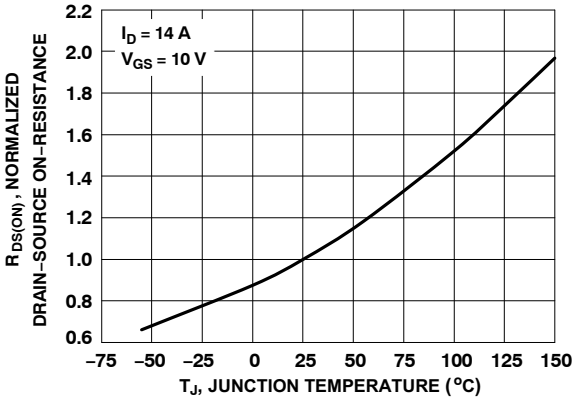


Figure 3. Normalized On Resistance vs. Junction Temperature

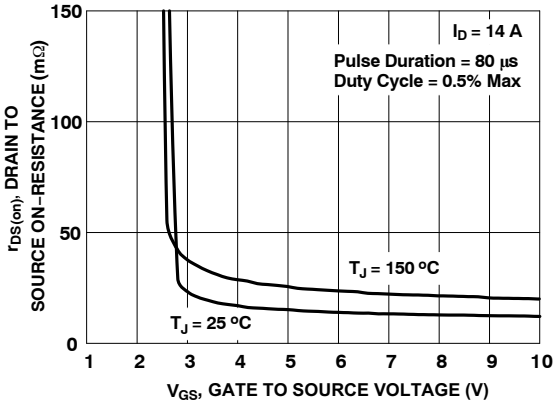


Figure 4. On-Resistance vs. Gate to Source Voltage

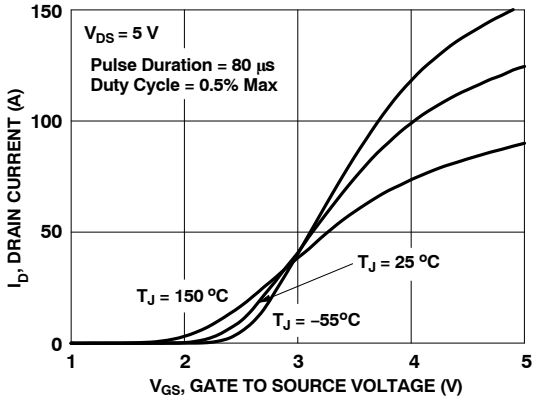


Figure 5. Transfer Characteristics

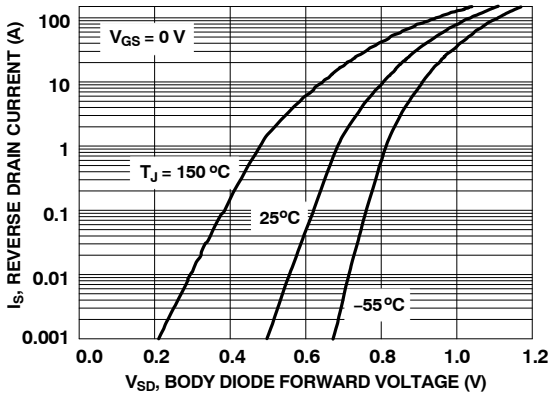


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

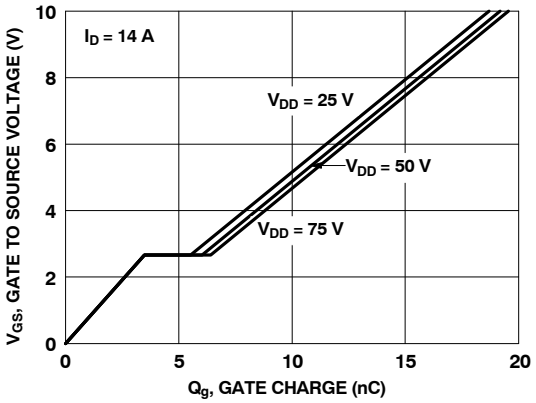


Figure 7. Gate Charge Characteristics

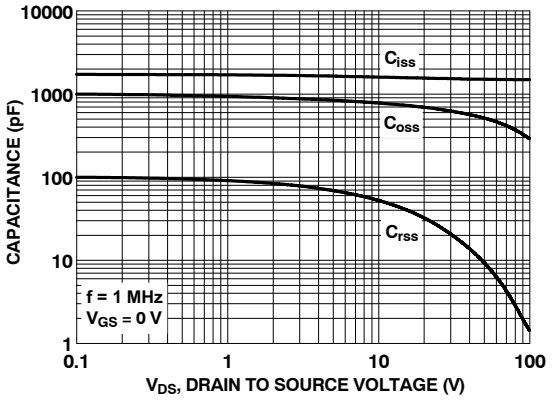


Figure 8. Capacitance vs. Drain to Source Voltage

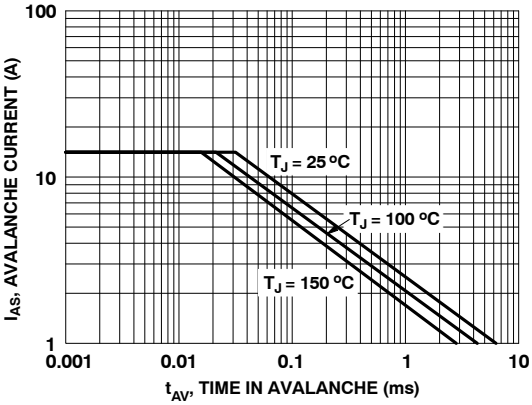


Figure 9. Unclamped Inductive Switching Capability

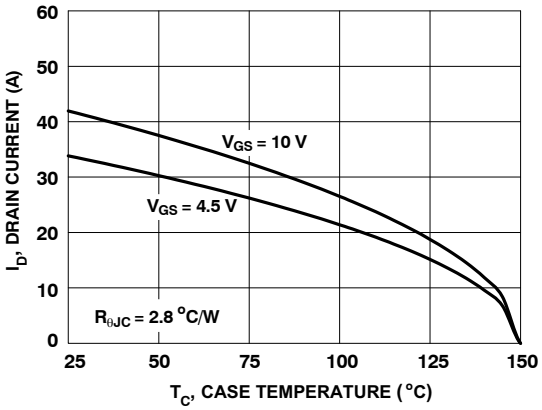


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

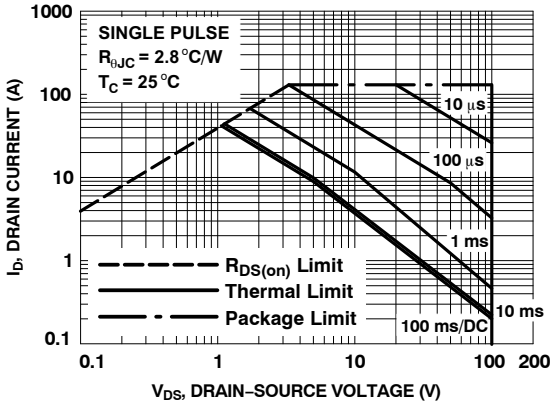


Figure 11. Forward Bias Safe Operating Area

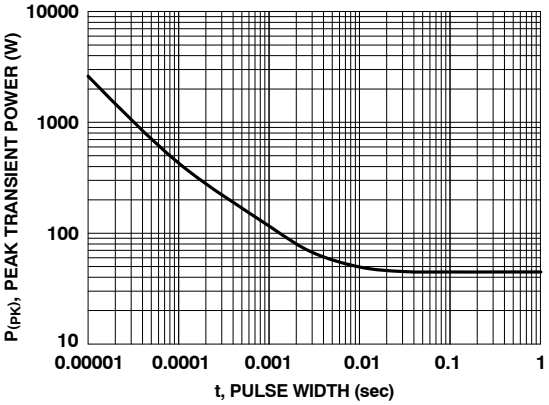


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

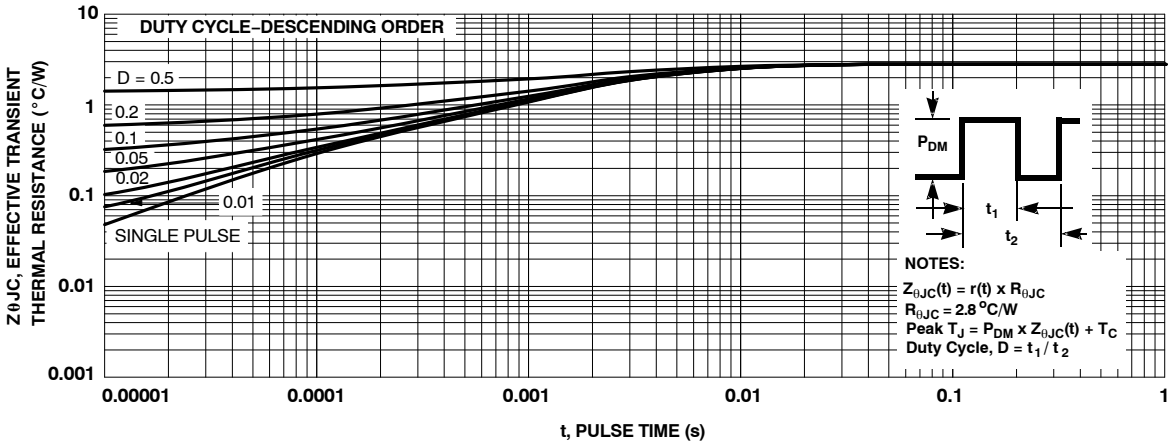
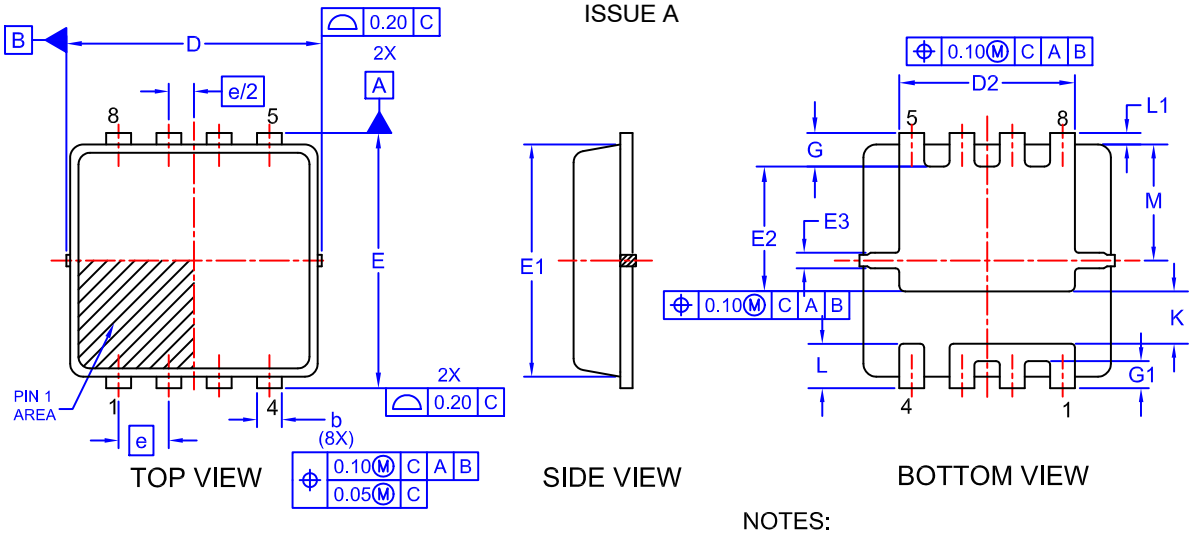


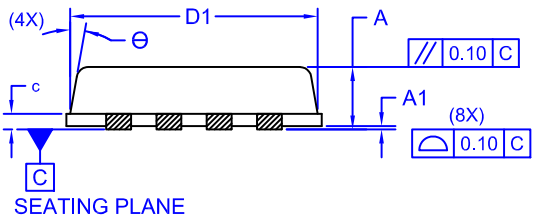
Figure 13. Junction−to−Case Transient Thermal Response Curve

PACKAGE DIMENSIONS

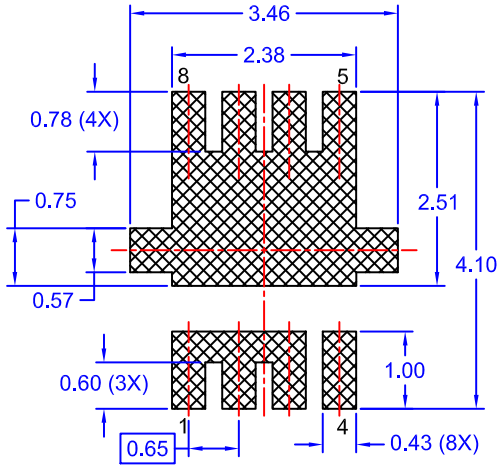
WDFN8 3.3x3.3, 0.65P
CASE 511DY
ISSUE A



NOTES:
1. CONTROLLING DIMENSION: MILLIMETERS
2. DIMENSIONS D1 & E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
b	0.23	0.33	0.43
c	0.15	0.20	0.25
D	3.20	3.30	3.40
D1	2.95	3.13	3.30
D2	1.98	2.20	2.40
E	3.20	3.30	3.40
E1	2.80	3.00	3.15
E2	1.40	1.60	1.80
E3	0.15	0.25	0.40
e	0.65 BSC		
G	0.30	0.43	0.55
G1	0.25	0.35	0.45
K	0.55	0.75	0.95
L	0.35	0.52	0.65
L1	0.06	0.15	0.30
M	1.35	1.50	1.60
θ	0	-	12



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